

# Citations for Ion : Zn

<b>Pub. Year</b>	<b>Authors, Title, Journal Citation and Comments</b>	<b>Citation Numb</b>
<b>1958</b>	Schmitt, R. A. Sharp, R. A. <b>'Measurement of the Range of Recoil Atoms'</b> <i>Phys. Rev. Letters, 1, 445-47 (1958)</i> <i>Comment : R. (33-130 keV) C, F, Cl, Ti, Fe, Zn, Cu, Mo, Ag, Au -&gt; Polystyrene, Teflon, Saran, Ti, Fe, Zn, Cu, Mo, Ag, Au</i>	<b>1958-Schm</b>
<b>1966</b>	Nielsen, O <b>'Specialeopgave'</b> <i>Niels Bohr Institute, University of Copenhagen, Pp. 1-64 (1966)</i> <i>Comment : S, dS. 50 keV C, Na, Cl, K, Mn, Y, Zn, Ag, Hf, Lu, Hg, Bi -&gt; H2, D2, He, N2, Ne, Ar</i>	<b>1966-Niel</b>
<b>1968</b>	Bowman, W. W. Lanzafame, F. M. Cline, C. K. Yu, Yu-Wen Blann, M. <b>'Recoil Ranges of 0.2 - 5.2 MeV Ions in Vanadium, Nickel, Iron, Zirconium and Gold.'</b> <i>Phys. Rev., 165, 485-93 (1968)</i> <i>Comment : R, dR. Ion(Z1=12-81, E=0.22-5.2 MeV) -&gt; V, Ni, Zr, Au</i>	<b>1968-Bowm</b>
<b>1970</b>	Santry, D. C. Sitter, C. W. <b>'Range and Retention Studies of 40-keV Ions in Solids, in H'</b> <i>Wagner, W. Walcher (Ed.) Proc. Int. Conf. Elmagn. Isotope Separators and Their Techniques. Marburg, P. 505-24 (1970)</i> <i>Comment : R, dR. 40 keV C, O, P, Co, Tl, Na, P, Co, Zn, Se, Kr, Hf, Cs, Ag, I, Xe -&gt; Au, W, WO3</i>	<b>1970-Sant</b>
<b>1973</b>	Chu, W. K. Crowder, B. L. Mayer, J. W. Ziegler, J. F. <b>'Range Distributions of Implanted Ions in SiO2, Si3N4, and Al2O3'</b> <i>Appl. Phys. Letters, 22, 490-92 (1973)</i> <i>Comment : R, dR. Zn, Ga, As, Se, Cd, Te (140-300 keV) -&gt; SiO2, Si3N4, Al2O3</i>	<b>1973-Chu</b>
<b>1973</b>	Chu, W. K. Crowder, B. L. Mayer, J. W. Ziegler, J. F. <b>'Ranges and Distributions of Ions Implanted into Dielectrics'</b> <i>B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 225-41 (1973)</i> <i>Comment : R.dR. (140-300 keV) Zn, Ga, As, Se, Cd, Te, Zn -&gt; Si, Si3N4, Al2O3</i>	<b>1973-Chu 2</b>
<b>1977</b>	Yu, P. W. Grant, J. T. Park, Y. S. Haas, T. W. <b>'Zn-Ion-Implantation Profiles in CuInSe2 by Auger Electron Spectroscopy'</b> <i>J. Appl. Phys., 48, 67-72 (1977)</i> <i>Comment : R. 120 keV Zn -&gt; CuInSe2</i>	<b>1977-Yu</b>
<b>1978</b>	Muller, G. Haubold, M. Schimko, R. Trapp, M. Schwarz, G. <b>'Investigations on the Diffusion of Implanted Zinc in GaAs(1-X)P(X) by Ion Microprobe'</b> <i>Phys. Stat. Sol. A, 49, 279-284 (1978)</i> <i>Comment : R. 100 keV Zn -&gt; GaAsP</i>	<b>1978-Mull</b>
<b>1979</b>	Inada, T. Kato, S. Maeda, Y. Tokunaga, K. <b>'Doping Profiles in Zn-Implanted GaAs after Laser Annealing'</b> <i>J. Appl. Phys., 50, 6000-6002 (1979)</i> <i>Comment : R, dR. 100 keV Zn -&gt; GaAs</i>	<b>1979-Inad</b>

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<b>1979</b>	Muller, G. Trapp, M. Schimko, R. Richter, C. E. <b>'Measurement of Range Distributions of Zinc and Nitrogen Ions in Multiple-Layer Substrates with Secondary Ion Microprobe'</b> <i>Phys. Stat. Sol. A, 51, 87-92 (1979)</i> <i>Comment : R, dR. 50-300 keV N, Zn -&gt;SiO<sub>2</sub>-GaAs(1-X)P(X), SiO<sub>2</sub>-Si<sub>3</sub>N<sub>4</sub></i>	<b>1979-Mull</b>
<b>1979</b>	Santry, D. C. Werner, R. D. Westcott, O. M. <b>'The Range of 120 keV Ions in Solids'</b> <i>IEEE Trans. Nucl. Sci., Ns-26, 1331-1334 (1979)</i> <i>Comment : R, dR. 120 keV Mg, Al, P, S, Cl, K, Ar, Cr, Mn, Cu, Zn, Ga, As, Br, Kr, Rb, Ag, In, Sn, Sb, Te, I, Xe, Cs, Ba, Pr, Au, Hg, Tl, Pb, Bi -&gt; Be, C, Al, Si</i>	<b>1979-Sant</b>
<b>1980</b>	Besenbacher, F. Bottiger, J. Laursen, T. Loftager, P. Moller, W. <b>'Z1-Oscillations in Low-Energy Heavy-Ion Ranges'</b> <i>Nucl. Inst. Methods, 170, 183-188 (1980)</i> <i>Comment : R, dR. Atomic Numbers 18-92 (epsilon=.015) -&gt; Si</i>	<b>1980-Bese2</b>
<b>1980</b>	Gamo, K. Yagita, H. Takai, M. Namba, S. Takigawa, M. <b>'Ion Implantation of Zn, Se, and Cd in BP Crystals'</b> <i>Rad. Effects, 47, 45-50 (1980)</i> <i>Comment : R, dR. 70 keV Zn, Se, Cd -&gt; BP (crystal)</i>	<b>1980-Gamo</b>
<b>1980</b>	Wampler, W. R. Follstaedt, D. M. Picraux, S. T. <b>'Electron Beam Annealing of Ion Implanted Al'</b> <i>Appl. Phys. Letters, 36, 366-368 (1980)</i> <i>Comment : R, dR. 150 keV Zn Sb -&gt; Al</i>	<b>1980-Wamp</b>
<b>1982</b>	Geissel, H. Laichter, YI Schneider, W. F. W. Armbruster, P. <b>'Energy Loss and Energy Loss Straggling of Fast Heavy Ions in Matter'</b> <i>Nucl. Inst. Methods, 194, 21-29 (1982)</i> <i>Comment : S. Heavy Ions (18 - 92) at 0.5-10 MeV/amu -&gt; 17 Solids and 5 Gases</i>	<b>1982-Geis</b>
<b>1996</b>	Gelfort, S. Kerkow, H. Stolle, R. Petukhov, V. P. Romanowski, E. A. <b>'Angular Dependence of the Electronic Energy Loss for Low Energy Heavy Ions under Channeling Conditions'</b> <i>Nucl. Inst. Methods, B115, 315-318 (1996)</i> <i>Comment : S. Channeling of ions He to Kr in Si &lt;110&gt;</i>	<b>1996-Gelf</b>
<b>2002</b>	Geissel, H. Weick, H. Scheidenberger, C. Bimbot, R. Gardes, D. <b>'Experimental Studies of Heavy-Ion Slowing Down in Matter'</b> <i>Nucl. Inst. Methods, B195, 3-54 (2002)</i> <i>Comment : S. Summary of 18 Heavy Ion Stopping in 26 Targets</i>	<b>2002-Geis</b>